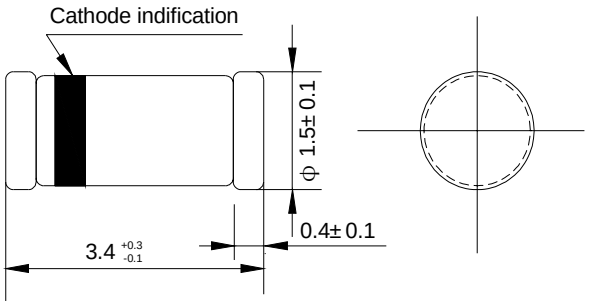
LL60/LL60P

Schottky Barrier Diodes

30-50 mAMPERES
40-45 VOLTS

MINI-MELF



Dimension in millimeters

Features

*Silicon Epitaxial Planner Diode
*Low Reverse Current and Low Forward Voltage
*Low Current Rectification and High Speed Switching
*High Reliability
*Used in Recorder, Radio, TV, Telephone as Detectors

Mechanical Data

*Case : MINI-MELF Glass Case (SOD-80)
*Polarity: Color Band Denotescathode Band
*Weight : Approx 0.05 gram

Maximum Ratings (T_A=25 °C Unless otherwise noted)

Characteristic	Symbol	LL60	LL60P	Unit
Pepetitive Peak Reverse Voltage	V_{RRM}	40	45	V
Non-Repetitive Peak Forward Surge Current @t=1S	I_{FSM}	150	500	mA
Forward Continuous Current, T_A =25°C	I_F	30	50	mA
Operating and Strorage Temperature Range	T_J , T_{STG}	-65 to +125		°C

Electrical Characteristics (T_A=25°C Unless otherwise noted)

Characteristic		Symbol	Min	Tpy	Max	Unit
Forward Voltage		V_F				V
I_F=1 mA	LL60		-	0.32	0.5	
	LL60P		-	0.24	0.5	
I_F=30 mA	LL60		-	0.65	1.0	
I_F=200 mA	LL60P		-	0.65	1.0	
Rverse Current		IR				uA
V_R=15V	LL60		-	0.1	0.5	
	LL60P		-	0.5	1.0	
Junction Capacitance		Cj				PF
V_R=1V, f=1MHz	LL60		-	2.0	-	
V_R=10V, f=1MHz	LL60P		-	6.0	-	
Reverse Recovery Time I_F=I_R=1mA , I_{rr}=1 mA, R_C=100 Ω		Trr	-	-	1.0	nS

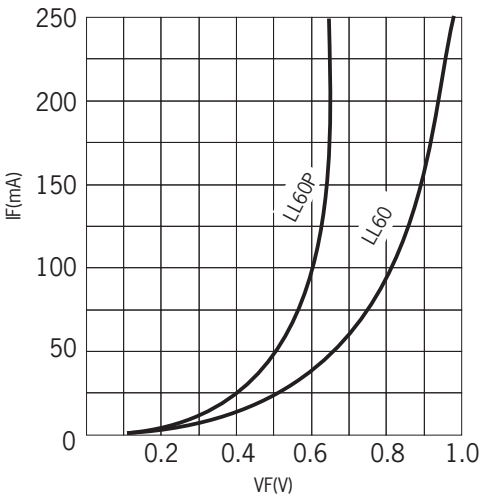


FIG.1 Fowrad Current vs. Forward Voltage

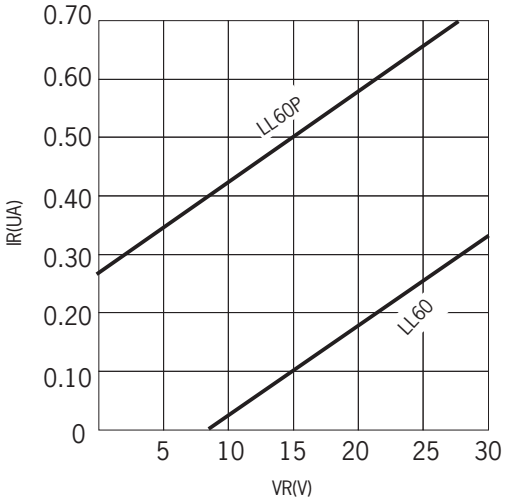


FIG.2 Reverse Current vs. Continuous Reverse Votlage

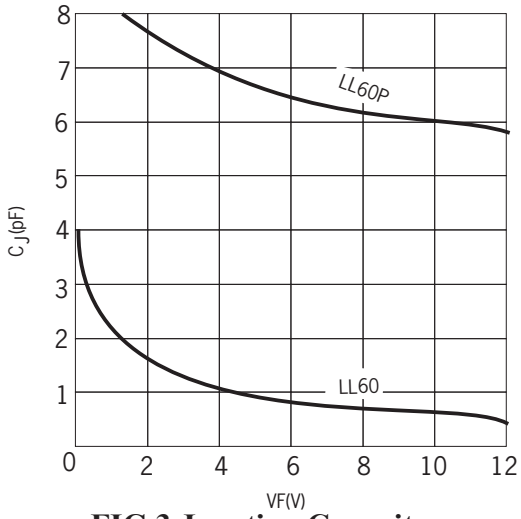


FIG.3 Junction Capacitance vs. Continuous Reverse Applied Voltage